

Schottky barrier diode

RB731U

●Applications

High speed switching.

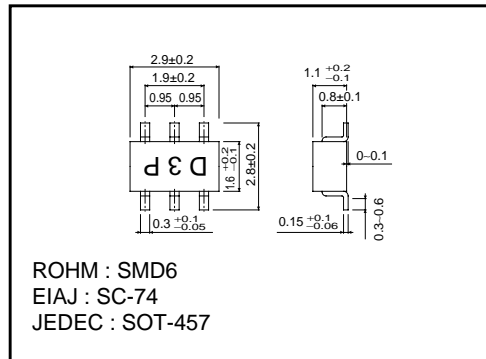
●Features

- 1) Small surface mounting type. (SMD6)
- 2) Low V_F and low I_R .
- 3) Three diodes in parallel for easy installation.

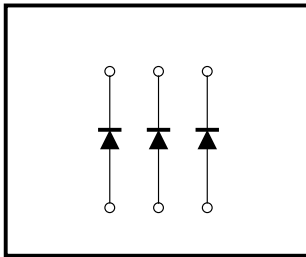
●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Circuit



●Absolute maximum ratings (Ta=25°C)

| Parameter | Symbol | Limits | Unit |
|-----------------------------|-----------|----------|------|
| Peak reverse voltage | V_{RM} | 40 | V |
| DC reverse voltage | V_R | 40 | V |
| Mean rectifying current | I_o | 30 | mA |
| Peak forward surge current* | I_{FSM} | 200 | mA |
| Junction temperature | T_j | 125 | °C |
| Storage temperature | T_{stg} | -40~+125 | °C |

* 60 Hz for 1

●Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|-------------------------------|--------|------|------|------|---------------|--------------------------------|
| Forward voltage | V_F | - | - | 0.37 | V | $I_F=1\text{mA}$ |
| Reverse current | I_R | - | - | 1 | μA | $V_R=10\text{V}$ |
| Capacitance between terminals | C_T | - | 2.0 | - | pF | $V_R=1\text{V}, f=1\text{MHz}$ |

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta=25°C)

